

2324-5

5 Watts, 24 Volts, Class C Microwave 2300-2400 MHz

The 2324- C, RF outp specifically application metalization	RAL DESCRIPTION -5 is a common base transistor capabl put power over the band 2300-2400 M y designed for Microwave Broadband ns. It includes Input and Output Pre M on and diffused ballasting to provide M s. The transistor uses a fully hermetic kage.	MHz. This transistor is I Class C amplifier Matching and utilizes gold high reliability and supreme	CASE OUTLINE 55AQ, STYLE 1
ABSO	LUTE MAXIMUM RATI	NGS	
	Power Dissipation @ 25°C	22 Watts	
Maximun	n Voltage and Current		
BVces	Collector to Emitter Voltage	40 Volts	
BVebo	Emitter to Base Voltage	3.5 Volts	
Ic	Collector Current	1.25 Amps	
M	n Temperatures		
waximun	Storage Temperature - 65 to + 200°C		
	emperature	-0010 ± 200 C	

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg Ir VSWR	Power Out Power Input Power Gain Efficiency Load Mismatch Tolerance	F = 2.3 - 2.4 GHz Vcc = 24 Volts	5 9.0 10:1	40	0.70	Watts Watts dB %

BVebo BVces Hfe Cob	Emitter to Base Breakdown Collector to Emitter Breakdown DC Current Gain Output Capacitance*	Ie = 10 mA Ie =50 mA Vce =5 V, Ic=160mA	3.5 40 20		Volts Volts
Rth	Thermal Resistance			8.0	°C/W

* Not measureable due to internal prematch network

Rev 1, April 1995

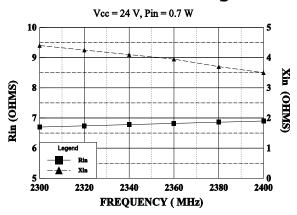
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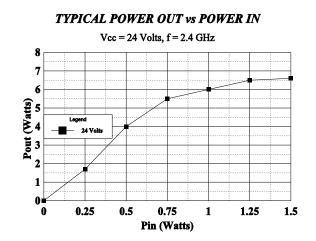
TYPICAL POWER OUT vs FREQUENCY Vcc = 24 V, Pin = 0.7 W8 6 P out (Watts) 2 Lege Pout 0 2250 2300 2350 2400 2450 **FREQUENCY (MHz)**

SERIES INPUT IMPEDANCE vs FREQUENCY



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SERIES LOAD IMPEDANCE vs FREQUENCY

